

MOSFETs Silicon N-channel MOS (U-MOSX-H)

TPH4R008QM

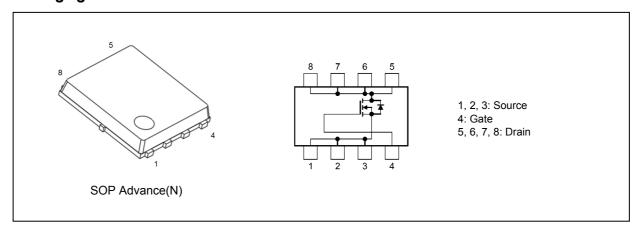
1. Applications

- · High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- · Motor Drivers

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 18 \text{ nC (typ.)}$
- (3) Small output charge: $Q_{oss} = 60 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 3.1 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (5) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 80 \text{ V)}$
- (6) Enhancement mode: $V_{th} = 2.5 \text{ to } 3.5 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 0.6 \text{ mA})$

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics	3		Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	80	V
Gate-source voltage			V_{GSS}	±20	
Drain current (DC)	(T _c = 25 °C)	(Note 1)	I _D	86	Α
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I _D	140	
Drain current (pulsed)	(t = 100 μs)	(Note 1)	I _{DP}	400	
Power dissipation	(T _c = 25 °C)		P_{D}	170	W
Power dissipation		(Note 3)	P _D	3	
Power dissipation	,	(Note 4)	P_{D}	0.96	
Single-pulse avalanche energy		(Note 5)	E _{AS}	67	mJ
Single-pulse avalanche current		(Note 5)	I _{AS}	86	Α
Channel temperature			T _{ch}	175	°C
Storage temperature			T _{stg}	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics			Symbol	Max	Unit
Channel-to-case thermal resistance	(T _c = 25 °C)		R _{th(ch-c)}	0.88	°C/W
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 3)	R _{th(ch-a)}	50	
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 4)	R _{th(ch-a)}	156	

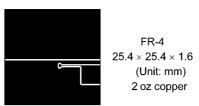
Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note 2: Limited by silicon chip capability.

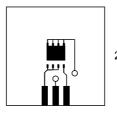
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_{DD} = 60 V, T_{ch} = 25 °C (initial), L = 7.7 μ H, I_{AS} =86 A







FR-4 $25.4 \times 25.4 \times 1.6$ (Unit: mm) 2 oz copper

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μΑ
Drain cut-off current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	80	_		V
Drain-source breakdown voltage (Note 6)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	60	_	_	
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 0.6 mA	2.5	_	3.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 6 V, I _D = 26 A	_	4	5.6	mΩ
		V _{GS} = 10 V, I _D = 43 A	_	3.1	4	

Note 6: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 40 V, V _{GS} = 0 V, f = 1 MHz	_	3750	5300	pF
Reverse transfer capacitance	C _{rss}		_	42	84	
Output capacitance	C _{oss}		_	900	_	
Gate resistance	r _g	_	_	1.6	2.4	Ω
Switching time (rise time)	t _r	See Fig. 6.2.1	_	16	_	ns
Switching time (turn-on time)	t _{on}		_	30	_	
Switching time (fall time)	t _f		_	20	_	
Switching time (turn-off time)	t _{off}		_	66	_	

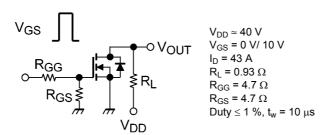


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Q_g	$V_{DD} \approx 40 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 43 \text{ A}$	_	57	1	nC
gate-drain)		$V_{DD} \approx 40 \text{ V}, V_{GS} = 6 \text{ V}, I_{D} = 26 \text{ A}$	_	35		
Gate-source charge 1	Q _{gs1}	$V_{DD} \approx 40 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 43 \text{ A}$	_	15		
Gate-drain charge	Q_{gd}		_	12.3		
Gate switch charge	Q_{SW}		_	18	_	
Output charge	Q_{oss}	V _{DS} = 40 V, V _{GS} = 0 V, f = 1 MHz	_	60		



6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 7)	I _{DRP}	(t = 100 μs)	_	_	400	Α
Diode forward voltage	V _{DSF}	I _{DR} = 86 A, V _{GS} = 0 V	_	_	-1.2	V
Reverse recovery time	t _{rr}	I_{DR} = 21.5 A, V_{GS} = 0 V,	_	49	_	ns
Reverse recovery charge	Q_{rr}	-dI _{DR} /dt = 100 A/μs	_	56		nC

Note 7: Ensure that the channel temperature does not exceed 175 °C.

7. Marking

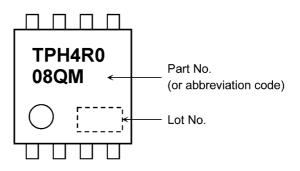


Fig. 7.1 Marking



8. Characteristics Curves (Note)

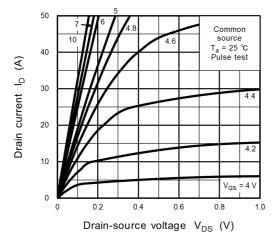


Fig. 8.1 I_D - V_{DS}

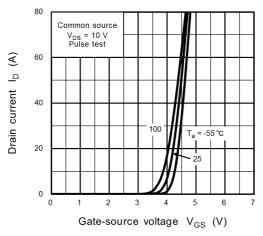


Fig. 8.3 $I_D - V_{GS}$

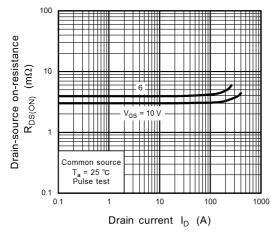


Fig. 8.5 R_{DS(ON)} - I_D

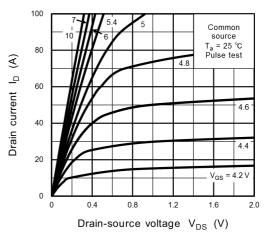


Fig. 8.2 I_D - V_{DS}

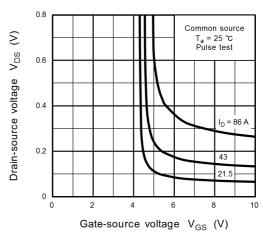


Fig. 8.4 V_{DS} - V_{GS}

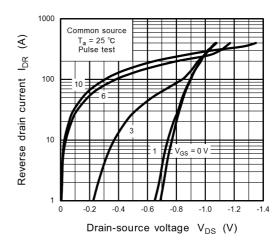


Fig. 8.6 I_{DR} - V_{DS}



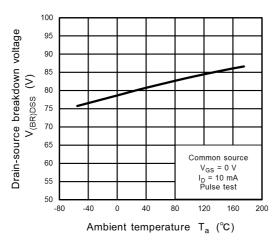


Fig. 8.7 V_{(BR)DSS} - T_a

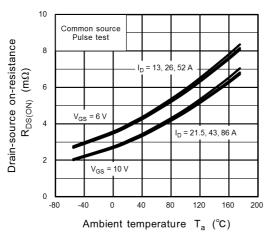


Fig. 8.9 R_{DS(ON)} - T_a

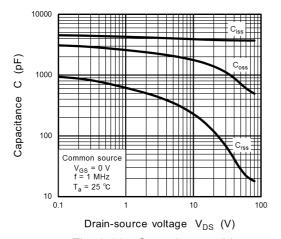


Fig. 8.11 Capacitance - V_{DS}

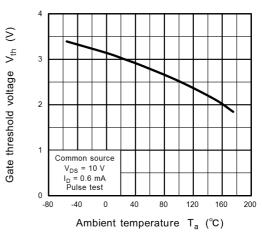


Fig. 8.8 V_{th} - T_a

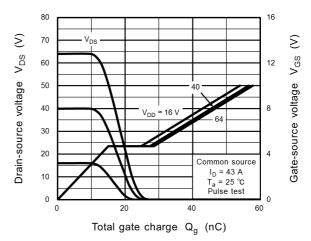


Fig. 8.10 Dynamic Input/Output Characteristics

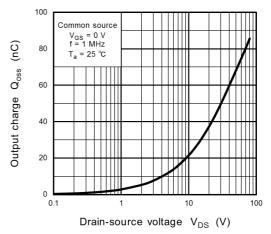


Fig. 8.12 Qoss - VDS



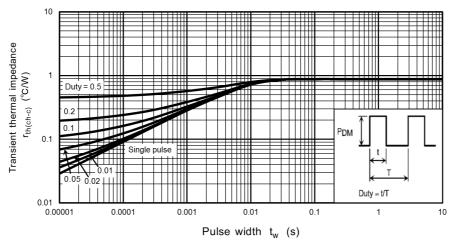


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

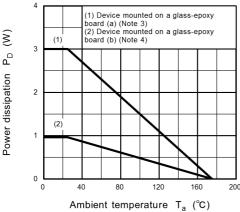


Fig. 8.14 P_D - T_a (Guaranteed Maximum)

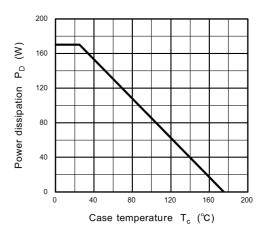


Fig. 8.15 P_D - T_c (Guaranteed Maximum)

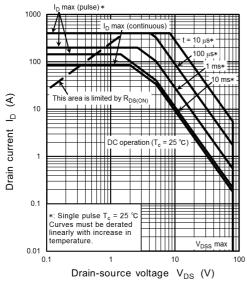


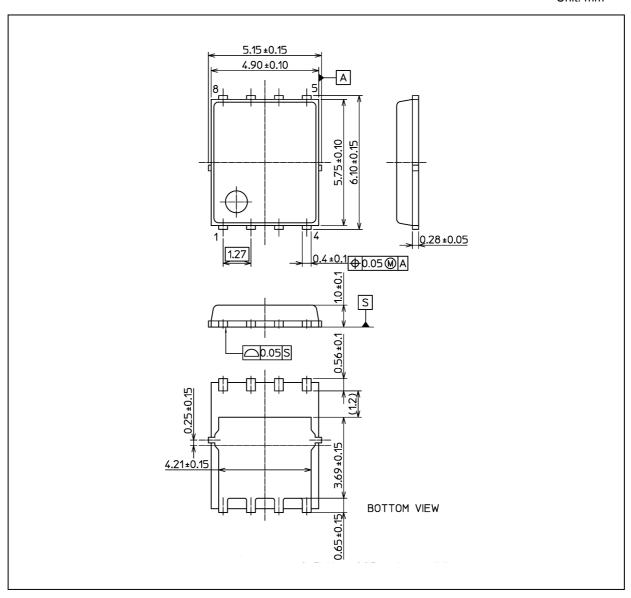
Fig. 8.16 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.105 g (typ.)

Package Name(s)
TOSHIBA: 2-5W1A
Nickname: SOP Advance(N)



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